

DATA SHEET

NEC

GaAs INTEGRATED CIRCUIT μ PG2131T5D

L-BAND PA DRIVER AMPLIFIER

DESCRIPTION

The μ PG2131T5D is GaAs MMIC for PA driver amplifier which were developed for dual band mobile phone and another L-band application. This device realizes high gain and high output power.

This device is housed in a 14-pin LGA (CSP Type) package. And this package is able to high-density surface mounting.

FEATURES

- Operation frequency : $f_{opt1} = 893$ to 960 MHz (0.8 GHz Band side)
: $f_{opt2} = 1\,429$ to $1\,453$ MHz (1.5 GHz Band side)
- Supply voltage : $V_{DD1,3} = 2.7$ to 2.9 V (2.8 V TYP.)
: $V_{DD2,4} = 3.2$ to 4.23 V (3.5 V TYP.)
- Circuit current : $I_{DD1} = 30$ mA TYP. @ $V_{DD1} = 2.8$ V, $V_{DD2} = 3.5$ V, $V_{AGC} = 2.5$ V, $P_{out} = +11$ dBm, (0.8 GHz Band side)
: $I_{DD2} = 30$ mA TYP. @ $V_{DD3} = 2.8$ V, $V_{DD4} = 3.5$ V, $V_{AGC} = 2.5$ V, $P_{out} = +11$ dBm, (1.5 GHz Band side)
- Output power : $P_{out1} = +14$ dBm TYP. @ $V_{DD1} = 2.8$ V, $V_{DD2} = 3.5$ V, $V_{AGC} = 2.5$ V (0.8 GHz Band side)
: $P_{out2} = -15$ dBm MAX. @ $V_{DD1} = 2.8$ V, $V_{DD2} = 3.5$ V, $V_{AGC} = 0.5$ V (0.8 GHz Band side)
: $P_{out3} = +14$ dBm TYP. @ $V_{DD3} = 2.8$ V, $V_{DD4} = 3.5$ V, $V_{AGC} = 2.5$ V (1.5 GHz Band side)
: $P_{out4} = -15$ dBm MAX. @ $V_{DD3} = 2.8$ V, $V_{DD4} = 3.5$ V, $V_{AGC} = 0.5$ V (1.5 GHz Band side)
- Low distortion : $P_{adj1} = -63$ dBc TYP. @ $V_{DD1} = 2.8$ V, $V_{DD2} = 3.5$ V, $V_{AGC} = 2.5$ V, $P_{out} = +11$ dBm,
 $f = 925$ MHz, $\Delta f = \pm 50$ kHz, 21 kHz Bandwidth (0.8 GHz Band side)
: $P_{adj3} = -63$ dBc TYP. @ $V_{DD3} = 2.8$ V, $V_{DD4} = 3.5$ V, $V_{AGC} = 2.5$ V, $P_{out} = +11$ dBm,
 $f = 1\,441$ MHz, $\Delta f = \pm 50$ kHz, 21 kHz Bandwidth (1.5 GHz Band side)
- High-density surface mounting : 14-pin LGA (CSP Type) package ($2.5 \times 2.5 \times 0.6$ mm)

APPLICATION

- Digital cellular: PDC 0.8/1.5 GHz Dual Band etc.

★ ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
μ PG2131T5D-E1	14-pin LGA (CSP Type)	G4B	<ul style="list-style-type: none">• Embossed tape 8 mm wide• Pin 6, 7 face the perforation side of the tape• Qty 3 kpcs/reel

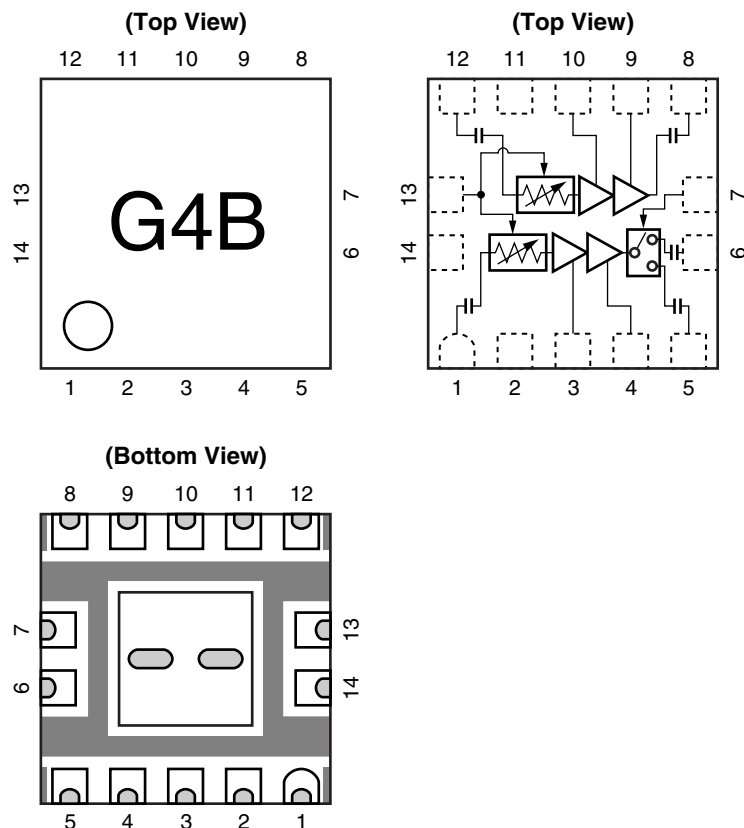
Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: μ PG2131T5D

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

★ PIN CONNECTIONS AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name
1	INPUT1 (0.8 GHz Band side)
2	GND
3	V _{DD1} (0.8 GHz Band side)
4	V _{DD2} (0.8 GHz Band side)
5	OUTPUT1 (0.8 GHz Band side)
6	OUTPUT2 (0.8 GHz Band side)
7	V _{SW} (0.8 GHz Band side)
8	OUTPUT3 (1.5 GHz Band side)
9	V _{DD4} (1.5 GHz Band side)
10	V _{DD3} (1.5 GHz Band side)
11	GND
12	INPUT2 (1.5 GHz Band side)
13	V _{AGC}
14	GND

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Supply Voltage 1, 2, 3, 4	V _{DD1, 2, 3, 4}	5.0	V
Gain Control Voltage	V _{AGC}	5.0	V
Switch Control Voltage	V _{SW}	5.0	V
Input Power 1 (1 pin)	P _{in1}	+10	dBm
Input Power 2 (12 pin)	P _{in2}	+10	dBm
Power Dissipation	P _D	140 ^{Note}	mW
Operating Ambient Temperature	T _A	-30 to +85	°C
Storage Temperature	T _{stg}	-40 to +150	°C

Note Mounted on double-sided copper-clad 50 × 50 × 1.6 mm epoxy glass PWB, T_A = +85°C

RECOMMENDED OPERATING RANGE (TA = +25°C, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Operating Frequency 1	f _{opt1}	893	–	960	MHz
Operating Frequency 2	f _{opt2}	1 429	–	1 453	MHz
Supply Voltage 1, 3	V _{DD1,3}	2.7	2.8	2.9	V
Supply Voltage 2, 4	V _{DD2,4}	3.2	3.5	4.23	V
Gain Control Voltage	V _{AGC}	0.5	–	2.5	V
Switch Control Voltage (High)	V _{SW (High)}	V _{DD1,3} -0.2	V _{DD1,3}	V _{DD1,3}	V
Switch Control Voltage (Low)	V _{SW (Low)}	0	0	0.2	V
Input Power 1 (1 pin)	P _{in1}	-10	–	0	dBm
Input Power 2 (12 pin)	P _{in2}	-10	–	0	dBm

ELECTRICAL CHARACTERISTICS

(TA = +25°C, V_{DD1,3} = 2.8 V, V_{DD2,4} = 3.5 V, π/4DQPSK modulated signal input, with external input and output matchig, unless otherwise specified)

0.8 GHz Band side

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Operating Frequency 1	f _{opt1}		893	–	960	MHz
Circuit Current 1	I _{DD1}	P _{out} = +11 dBm, V _{AGC} = 2.5 V	–	30	37	mA
Output Power 1	P _{out1}	P _{in} = -10 to 0 dBm, V _{AGC} = 2.5 V	+12	+14	–	dBm
Output Power 2	P _{out2}	P _{in} = -10 to 0 dBm, V _{AGC} = 0.5 V	–	–	-15	dBm
Adjacent Channel Power Leakage 1	P _{adj1}	P _{out} = +11 dBm, V _{AGC} = 2.5 V, P _{in} = -10 to 0 dBm, Δf = ±50 kHz, 21 kHz Bandwidth	–	-63	-58	dBc
Adjacent Channel Power Leakage 2	P _{adj2}	P _{out} = +11 dBm, V _{AGC} = 2.5 V, P _{in} = -10 to 0 dBm, Δf = ±100 kHz, 21 kHz Bandwidth	–	-72	-69	dBc
Noise Figure 1	NF ₁	V _{AGC} = 2.5 V	–	6	–	dB

1.5 GHz Band side

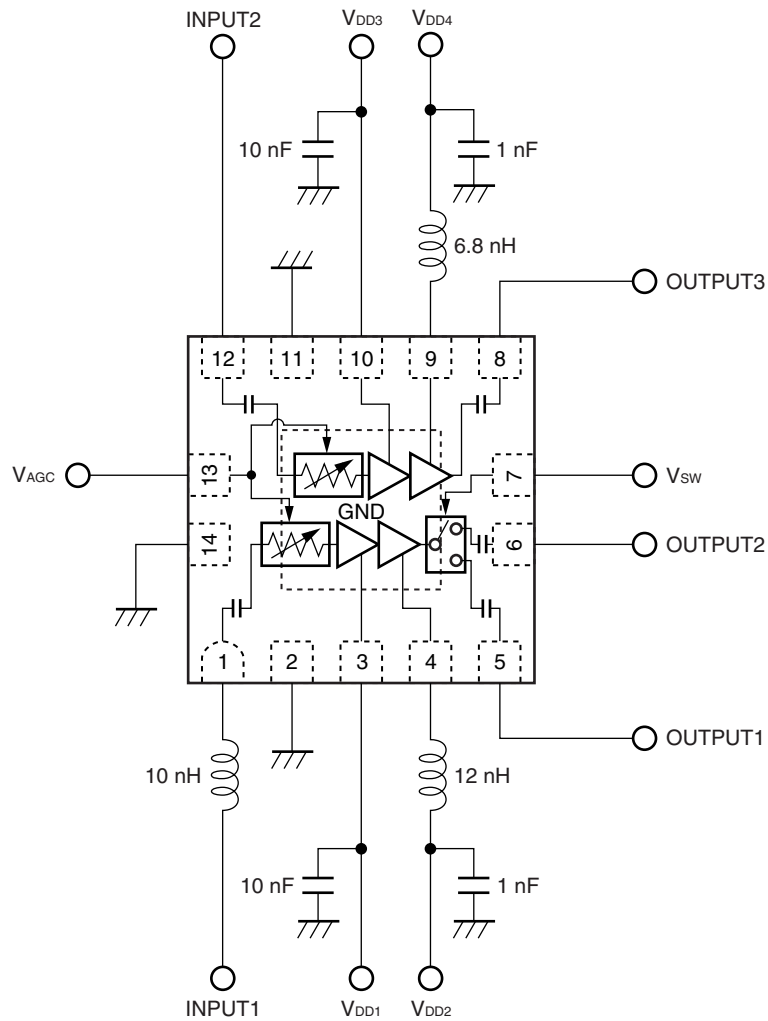
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Operating Frequency 2	f _{opt2}		1 429	–	1 453	MHz
Circuit Current 2	I _{DD2}	P _{out} = +11 dBm, V _{AGC} = 2.5 V	–	30	37	mA
Output Power 3	P _{out3}	P _{in} = -10 to 0 dBm, V _{AGC} = 2.5 V	+12	+14	–	dBm
Output Power 4	P _{out4}	P _{in} = -10 to 0 dBm, V _{AGC} = 0.5 V	–	–	-15	dBm
Adjacent Channel Power Leakage 3	P _{adj3}	P _{out} = +11 dBm, V _{AGC} = 2.5 V, P _{in} = -10 to 0 dBm, Δf = ±50 kHz, 21 kHz Bandwidth	–	-63	-58	dBc
Adjacent Channel Power Leakage 4	P _{adj4}	P _{out} = +11 dBm, V _{AGC} = 2.5 V, P _{in} = -10 to 0 dBm, Δf = ±100 kHz, 21 kHz Bandwidth	–	-72	-69	dBc
Noise Figure 2	NF ₂	V _{AGC} = 2.5 V	–	6	–	dB

0.8 GHz/1.5 GHz Band side

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gain Control Current	I _{AGC}	V _{DD1,3} = 2.8/0 V, V _{DD2,4} = 3.5/0 V, V _{AGC} = 0.5/2.5 V	-100	-	300	μA
Switch Control Current	I _{SW}	V _{SW} = 2.8/0 V	-10	-	100	μA

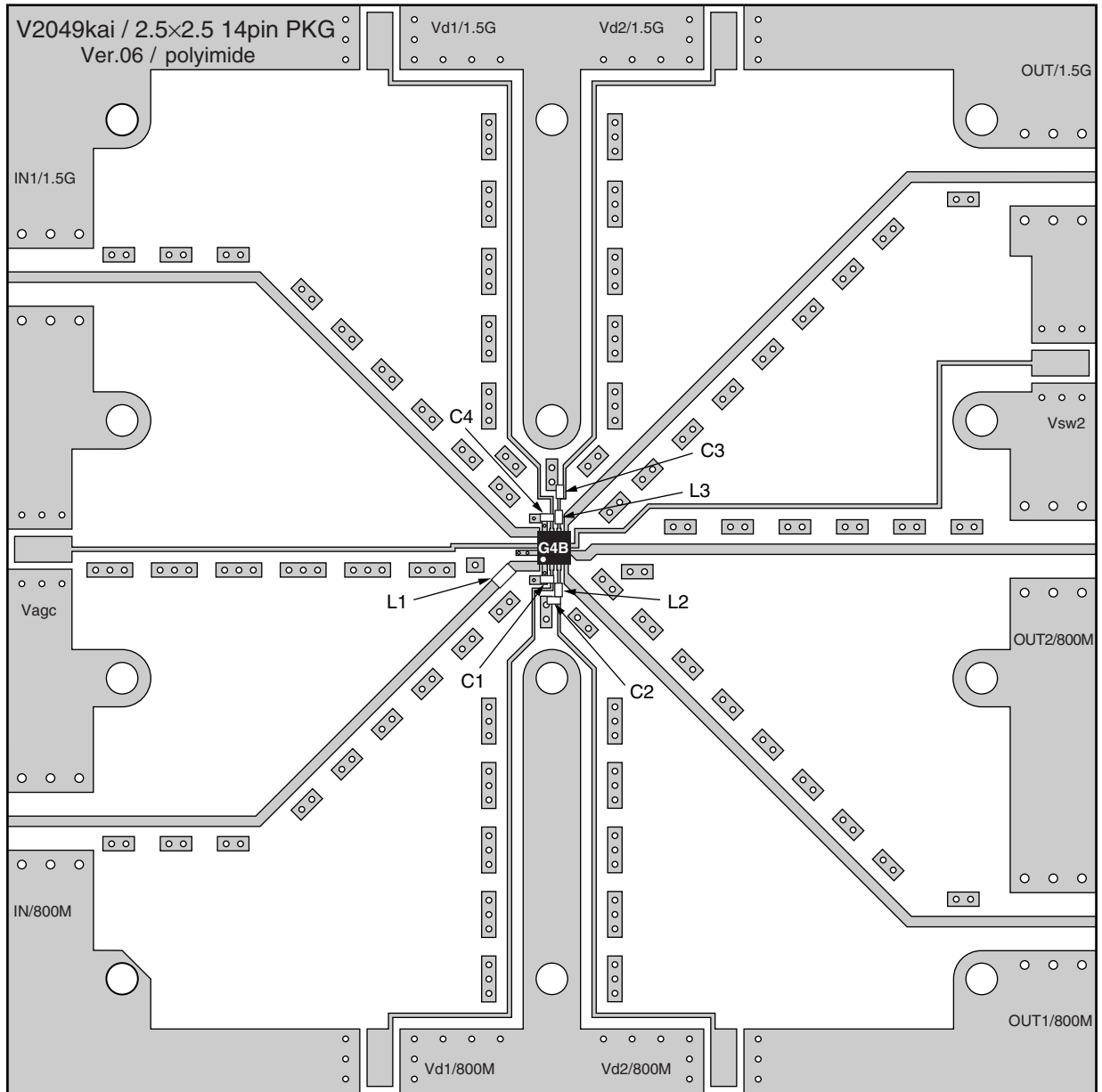
EVALUATION CIRCUIT

($f_{opt1} = 893$ to 960 MHz, $f_{opt2} = 1\,429$ to $1\,453$ MHz, $V_{DD1,3} = 2.8$ V, $V_{DD2,4} = 3.5$ V)



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

★ ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



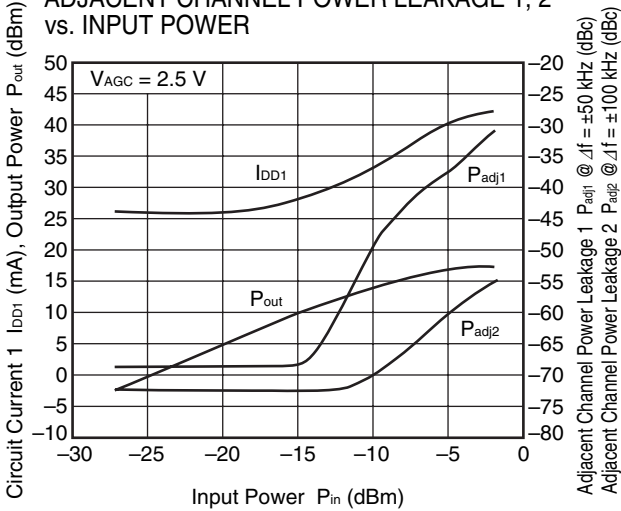
USING THE NEC EVALUATION BOARD

Symbol	Values
L1	10 nH
L2	12 nH
L3	6.8 nH
C1, C4	10 nF
C2, C3	1 nF

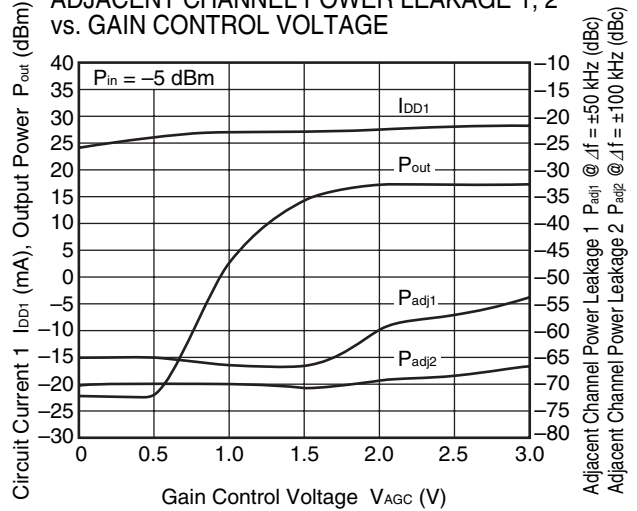
TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

0.8 GHz Band side (INPUT1–OUTPUT1, f = 960 MHz, VDD1 = 2.8 V, VDD2 = 3.5 V, VSW = 0 V)

CIRCUIT CURRENT 1, OUTPUT POWER, ADJACENT CHANNEL POWER LEAKAGE 1, 2 vs. INPUT POWER

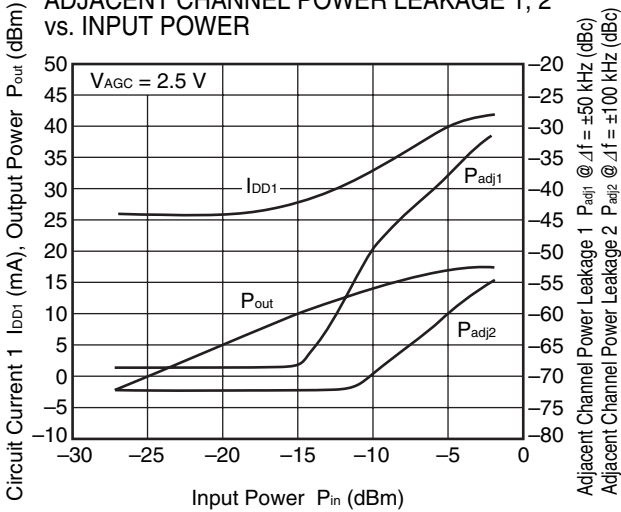


CIRCUIT CURRENT 1, OUTPUT POWER, ADJACENT CHANNEL POWER LEAKAGE 1, 2 vs. GAIN CONTROL VOLTAGE

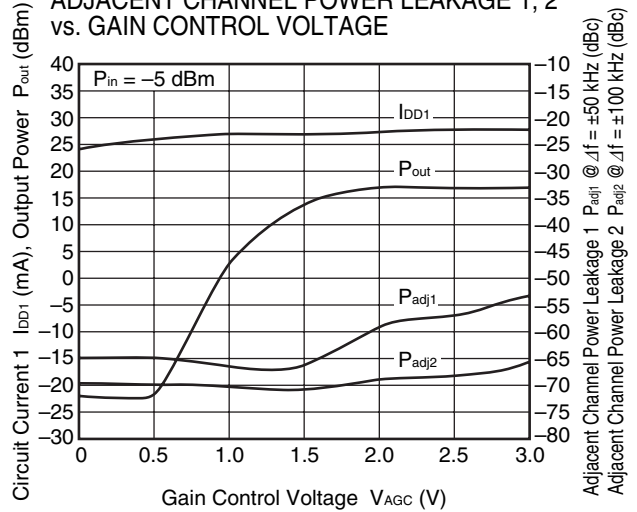


0.8 GHz Band side (INPUT1–OUTPUT2, f = 960 MHz, VDD1 = 2.8 V, VDD2 = 3.5 V, VSW = 2.8 V)

CIRCUIT CURRENT 1, OUTPUT POWER, ADJACENT CHANNEL POWER LEAKAGE 1, 2 vs. INPUT POWER

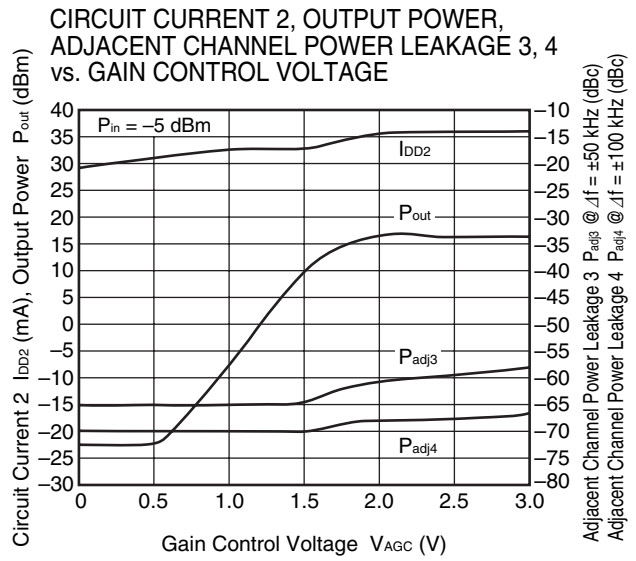
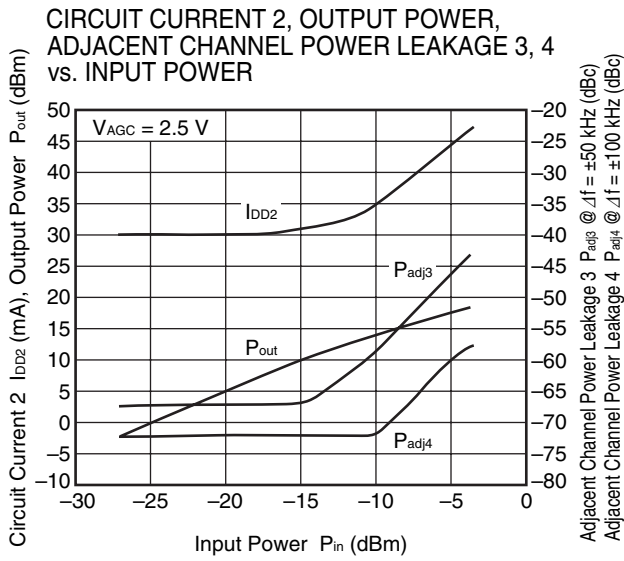


CIRCUIT CURRENT 1, OUTPUT POWER, ADJACENT CHANNEL POWER LEAKAGE 1, 2 vs. GAIN CONTROL VOLTAGE



Remark The graphs indicate nominal characteristics.

1.5 GHz Band side (INPUT2-OUTPUT3, $f = 1\ 453\ \text{MHz}$, $V_{DD3} = 2.8\ \text{V}$, $V_{DD4} = 3.5\ \text{V}$)



Remark The graphs indicate nominal characteristics.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) : 215°C or below Time at temperature of 200°C or higher : 25 to 40 seconds Preheating time at 120 to 150°C : 30 to 60 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) : 260°C or below Time at peak temperature : 10 seconds or less Preheating temperature (package surface temperature) : 120°C or below Maximum number of flow processes : 1 time Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) : 350°C or below Soldering time (per side of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

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M8E 00.4-0110

<p>Caution</p>	<p>GaAs Products</p>	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"> • Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below. <ol style="list-style-type: none"> 1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials. 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal. • Do not burn, destroy, cut, crush, or chemically dissolve the product. • Do not lick the product or in any way allow it to enter the mouth.
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► For further information, please contact

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